

## Low VCE(sat) transistor(80V,0.7A)

#### Features

- Low VCE(sat).
- Excellent DC current gain characteristics.
- Complements the 2SB1386
- RoHS compliant package

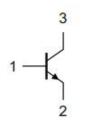
#### Packing & Order Information

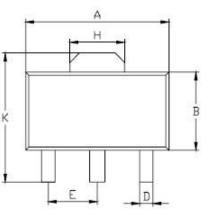
3,000/Reel

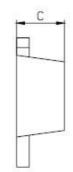


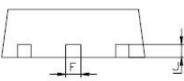


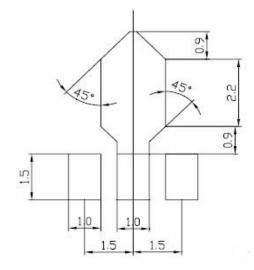
#### **Graphic symbol**











Dim	Min	Max
Α	4.5	4.7
В	2.3	2.7
С	1.5Ty	/pical
D	0.35	0.55
Е	1.4	1.6
F	0.4	0.6
н	1.55	1.75
J	0.4Typical	
К	4.15	4.25



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#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)					
Symbol	Parameter	Value	Unit		
V <sub>CBO</sub>	Collector-Base Voltage	50	V		
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V		
V <sub>EBO</sub>	Emitter-Base Voltage	6	V		
I <sub>C</sub>	Collector Current	5	A		
P <sub>C</sub>	Collector Dissipation	500	mW		
Tj,Tstg	Junction and Storage Temperature	-55 to +150	°C		

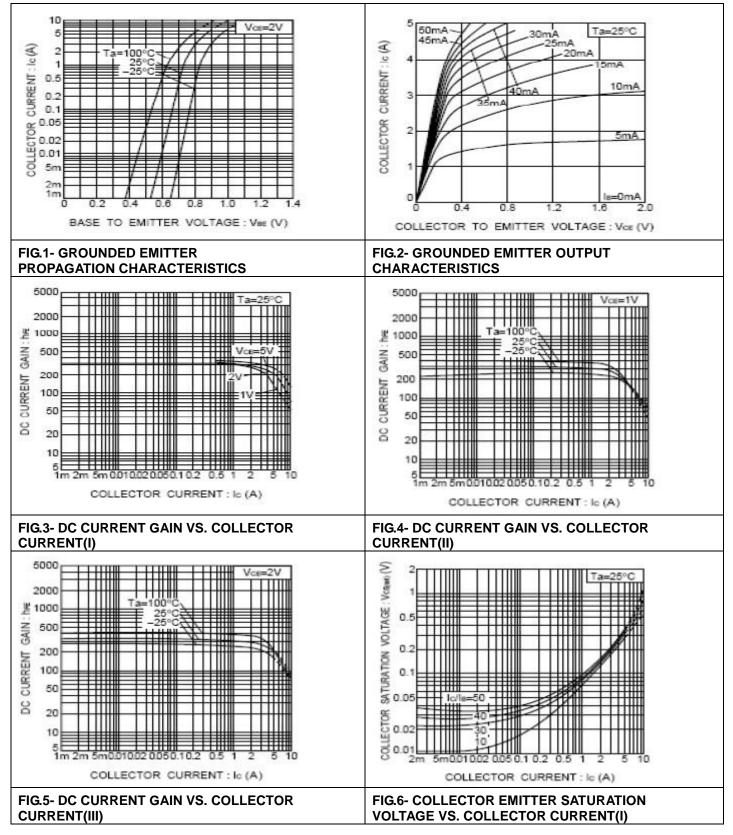
ELECTRI	ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified						
Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT	
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_{C} = 50 \mu A$ , $I_{E} = 0$	50			V	
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_{\rm C} = 1 \text{ mA}$ , $I_{\rm B} = 0$	20			V	
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_{E} = 50 \mu A$ , $I_{C} = 0$	6			V	
I <sub>CBO</sub>	Collector cut-off current	$V_{CB} = 40 \text{ V}$ , $I_E = 0$			0.5	μA	
I <sub>EBO</sub>	Emitter cut-off current	$V_{EB} = 5 V$ , $I_C = 0$			0.5	μA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 V$ , $I_C = 0.5 A$	120		390		
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$I_{\rm C} = 4  {\rm A}  ,  I_{\rm B} = 0.1  {\rm A}$		0.25	1.0	V	
f⊤	Transition frequency	$V_{CE} = 6 V$ , $I_C = 50 mA$ f = 100MHz		150		MHz	
C <sub>ob</sub>	Collector output capacitance	$V_{CB} = 20 \text{ V}$ , $I_E = 0$ f = 1.0MHz		30		pF	

CLASSIFICATION OF h <sub>FE</sub>					
Marking	AHQ	AHR			
Rank	Q	R			
Range	120-270	180-390			



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■TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





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